

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1 - 40 (Cancelled)

41. (New) A set of masks comprising:
- a first mask having a first pattern to expose a line having a width in a radiation sensitive layer; and
- a second mask having a second pattern to reduce the width of the line.
42. (New) The set of masks of claim 41, wherein the first pattern comprises a first opaque line, and wherein the second pattern comprises a second opaque line that overlaps the first opaque line.
43. (New) The set of masks of claim 42, wherein the opaque lines have the same width.
44. (New) The set of masks of claim 43, wherein the opaque lines overlap by half their width.
45. (New) The set of masks of claim 41:
- wherein the first pattern comprises a first low transmittance region to transmit comparatively low intensity radiation to the radiation sensitive layer, and a first high transmittance region to transmit comparatively high intensity radiation to the radiation sensitive layer; and

wherein the second pattern comprises a second high transmittance region that corresponds to the first low transmittance region and a second low transmittance region that corresponds to the first high transmittance region.

46. (New) The set of masks of claim 41, further comprising:
- a portion of the first mask to expose a feature in the radiation sensitive layer; and
- a portion of the second mask to add a structural feature to the exposed feature.
47. (New) The set of masks of claim 41, further comprising:
- a portion of the first mask to expose a feature in the radiation sensitive layer; and
- a radiation intensity reducer of the second mask to reduce a subwavelength distortion of the exposed feature.
48. (New) The set of masks of claim 47, wherein the radiation intensity reducer comprises an arrangement of opaque subresolution shapes.
49. (New) The set of masks of claim 47, wherein the radiation intensity reducer comprises a film including at least one of molybdenum silicide and chromium fluoride.
50. (New) A set of masks comprising:
- a first mask having a first pattern to expose a feature in a radiation sensitive layer;
- and
- a second mask having a second pattern to add a structural feature to the exposed feature.

51. (New) The set of masks of claim 50, further comprising:
- a first opaque line of the first mask to expose a line having a width in the radiation sensitive layer; and
- a second opaque line of the second mask that overlaps with the first opaque line to reduce the width of the line.
52. (New) The set of masks of claim 50, further comprising:
- low and high transmittance regions of the first mask to expose a second feature in the radiation sensitive layer; and
- low and high transmittance regions of the second mask that are reversed relative to the regions of the first mask to reduce a pattern shift distortion of the second feature.
53. (New) The set of masks of claim 50, further comprising:
- a portion of the first mask to expose a second feature in the radiation sensitive layer; and
- a radiation intensity reducer of the second mask to reduce a subwavelength distortion of the second feature.
54. (New) A set of masks comprising:
- a first mask having a first low transmittance region to transmit comparatively low intensity radiation to the radiation sensitive layer and a first high transmittance region to transmit comparatively high intensity radiation to the radiation sensitive layer; and

a second mask having a second high transmittance region that corresponds to the first low transmittance region and a second low transmittance region that corresponds to the first high transmittance region.

55. (New) The set of masks of claim 54, further comprising:

a portion of the first mask to expose a second feature in the radiation sensitive layer; and

a portion of the second mask to add a structural feature to the second feature.

56. (New) The set of masks of claim 54, further comprising:

a portion of the first mask to expose a second feature in the radiation sensitive layer; and

a radiation intensity reducer of the second mask to reduce a subwavelength distortion of the second feature.

57. (New) The set of masks of claim 54, further comprising:

a first opaque line of the first mask to expose a line having a width in the radiation sensitive layer; and

a second opaque line of the second mask to reduce the width of the line.